

36-Mbit DDR II SIO SRAM Two-Word Burst Architecture

Features

- 36-Mbit density (2M × 18, 1M × 36)
- 333 MHz clock for high bandwidth
- Two-word burst for reducing address bus frequency
- Double data rate (DDR) interfaces (data transferred at 666 MHz) at 333 MHz
- Two input clocks (K and \bar{K}) for precise DDR timing
 - SRAM uses rising edges only
- Two input clocks for output data (C and \bar{C}) to minimize clock skew and flight time mismatches
- Echo clocks (CQ and \bar{CQ}) simplify data capture in high speed systems
- Synchronous internally self timed writes
- DDR II operates with 1.5 cycle read latency when \overline{DOFF} is asserted HIGH
- Operates similar to DDR I device with 1 cycle read latency when \overline{DOFF} is asserted LOW
- 1.8 V core power supply with HSTL inputs and outputs
- Variable drive HSTL output buffers
- Expanded HSTL output voltage (1.4 V to V_{DD})
 - Supports both 1.5 V and 1.8 V IO supply
- Available in 165-ball FBGA package (13 × 15 × 1.4 mm)
- Offered in both Pb-free and non Pb-free packages
- JTAG 1149.1 compatible test access port
- Phase locked loop (PLL) for accurate data placement

Configurations

CY7C1423KV18 – 2M × 18

CY7C1424KV18 – 1M × 36

Functional Description

The CY7C1423KV18, and CY7C1424KV18 are 1.8 V synchronous pipelined SRAMs, equipped with DDR II SIO (double data rate separate I/O) architecture. The DDR II SIO consists of two separate ports: the read port and the write port to access the memory array. The read port has data outputs to support read operations and the write port has data inputs to support write operations. The DDR II SIO has separate data inputs and data outputs to completely eliminate the need to “turnaround” the data bus required with common I/O devices. Access to each port is accomplished through a common address bus. Addresses for read and write are latched on alternate rising edges of the input (K) clock. Write data is registered on the rising edges of both K and \bar{K} . Read data is driven on the rising edges of C and \bar{C} if provided, or on the rising edge of K and \bar{K} if C/ \bar{C} are not provided. Each address location is associated with two 18-bit words in the case of CY7C1423KV18, and two 36-bit words in the case of CY7C1424KV18 that burst sequentially into or out of the device.

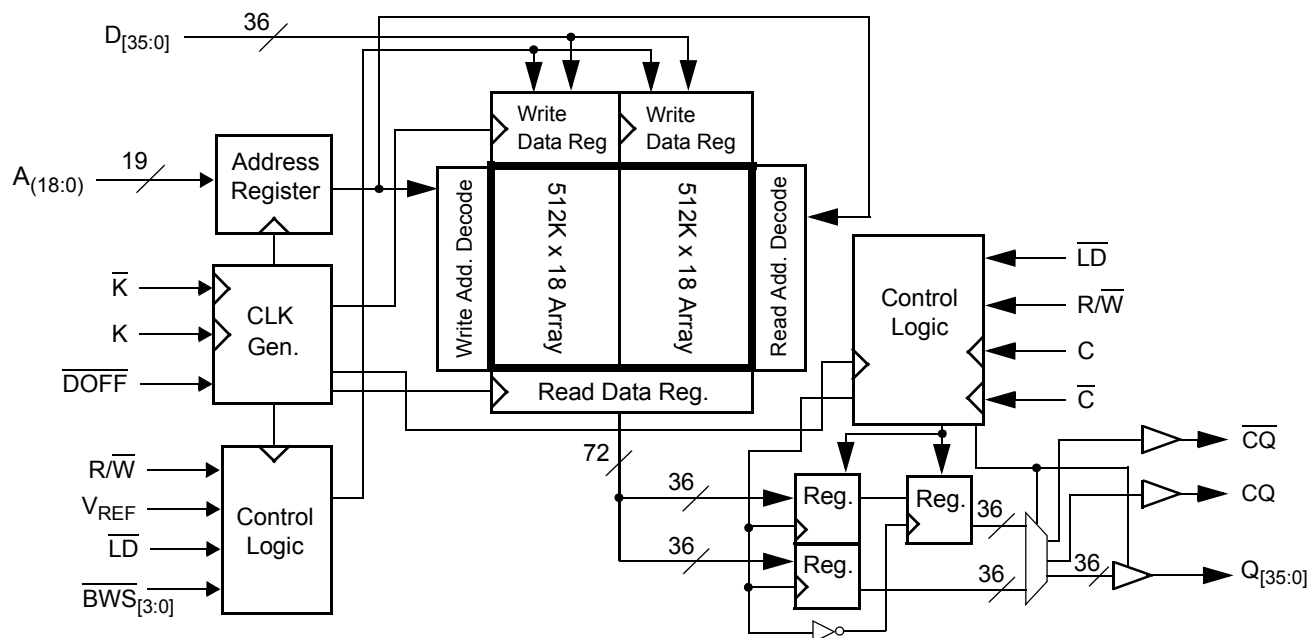
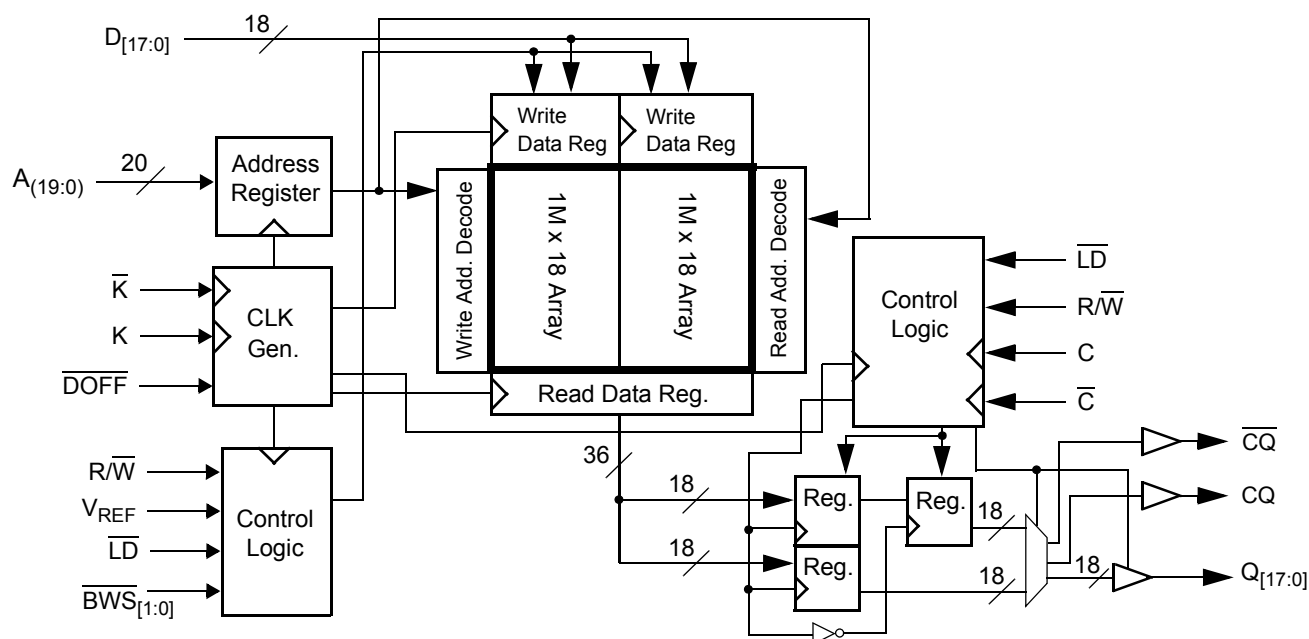
Asynchronous inputs include an output impedance matching input (ZQ). Synchronous data outputs are tightly matched to the two output echo clocks CQ/ \bar{CQ} , eliminating the need to capture data separately from each individual DDR II SIO SRAM in the system design. Output data clocks (C/ \bar{C}) enable maximum system clocking and data synchronization flexibility.

All synchronous inputs pass through input registers controlled by the K or \bar{K} input clocks. All data outputs pass through output registers controlled by the C or \bar{C} (or K or \bar{K} in a single clock domain) input clocks. Writes are conducted with on-chip synchronous self-timed write circuitry.

For a complete list of related documentation, click [here](#).

Selection Guide

Description		333 MHz	300 MHz	250 MHz	Unit
Maximum operating frequency		333	300	250	MHz
Maximum operating current	× 18	490	460	430	mA
	× 36	600	Not Offered	490	



Contents

Pin Configurations	4	Boundary Scan Order	18
Pin Definitions	5	Power Up Sequence in DDR II SRAM	19
Functional Overview	6	Power Up Sequence	19
Read Operations	6	PLL Constraints	19
Write Operations	6	Maximum Ratings	20
Byte Write Operations	7	Operating Range	20
Single Clock Mode	7	Neutron Soft Error Immunity	20
DDR Operation	7	Electrical Characteristics	20
Depth Expansion	7	DC Electrical Characteristics	20
Programmable Impedance	7	AC Electrical Characteristics	22
Echo Clocks	7	Capacitance	22
PLL	7	Thermal Resistance	22
Application Example	8	AC Test Loads and Waveforms	22
Truth Table	9	Switching Characteristics	23
Write Cycle Descriptions	9	Switching Waveforms	25
Write Cycle Descriptions	10	Ordering Information	26
IEEE 1149.1 Serial Boundary Scan (JTAG)	11	Ordering Code Definitions	26
Disabling the JTAG Feature	11	Package Diagram	27
Test Access Port	11	Acronyms	28
Performing a TAP Reset	11	Document Conventions	28
TAP Registers	11	Units of Measure	28
TAP Instruction Set	11	Document History Page	29
TAP Controller State Diagram	13	Sales, Solutions, and Legal Information	31
TAP Controller Block Diagram	14	Worldwide Sales and Design Support	31
TAP Electrical Characteristics	14	Products	31
TAP AC Switching Characteristics	15	PSoC@Solutions	31
TAP Timing and Test Conditions	16	Cypress Developer Community	31
Identification Register Definitions	17	Technical Support	31
Scan Register Sizes	17		
Instruction Codes	17		

Pin Configurations

The pin configurations for CY7C1423KV18 and CY7C1424KV18 follow. [1]

Figure 1. 165-ball FBGA (13 × 15 × 1.4 mm) pinout

CY7C1423KV18 (2M × 18)

	1	2	3	4	5	6	7	8	9	10	11
A	$\overline{\text{CQ}}$	NC/144M	A	$\overline{\text{R/W}}$	$\overline{\text{BWS}}_1$	$\overline{\text{K}}$	NC/288M	$\overline{\text{LD}}$	A	NC/72M	CQ
B	NC	Q9	D9	A	NC	K	$\overline{\text{BWS}}_0$	A	NC	NC	Q8
C	NC	NC	D10	V_{SS}	A	A	A	V_{SS}	NC	Q7	D8
D	NC	D11	Q10	V_{SS}	V_{SS}	V_{SS}	V_{SS}	V_{SS}	NC	NC	D7
E	NC	NC	Q11	V_{DDQ}	V_{SS}	V_{SS}	V_{SS}	V_{DDQ}	NC	D6	Q6
F	NC	Q12	D12	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	NC	NC	Q5
G	NC	D13	Q13	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	NC	NC	D5
H	$\overline{\text{DOFF}}$	V_{REF}	V_{DDQ}	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	V_{DDQ}	V_{REF}	ZQ
J	NC	NC	D14	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	NC	Q4	D4
K	NC	NC	Q14	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	NC	D3	Q3
L	NC	Q15	D15	V_{DDQ}	V_{SS}	V_{SS}	V_{SS}	V_{DDQ}	NC	NC	Q2
M	NC	NC	D16	V_{SS}	V_{SS}	V_{SS}	V_{SS}	V_{SS}	NC	Q1	D2
N	NC	D17	Q16	V_{SS}	A	A	A	V_{SS}	NC	NC	D1
P	NC	NC	Q17	A	A	C	A	A	NC	D0	Q0
R	TDO	TCK	A	A	A	$\overline{\text{C}}$	A	A	A	TMS	TDI

CY7C1424KV18 (1M × 36)

	1	2	3	4	5	6	7	8	9	10	11
A	$\overline{\text{CQ}}$	NC/288M	NC/72M	$\overline{\text{R/W}}$	$\overline{\text{BWS}}_2$	$\overline{\text{K}}$	$\overline{\text{BWS}}_1$	$\overline{\text{LD}}$	A	NC/144M	CQ
B	Q27	Q18	D18	A	$\overline{\text{BWS}}_3$	K	$\overline{\text{BWS}}_0$	A	D17	Q17	Q8
C	D27	Q28	D19	V_{SS}	A	A	A	V_{SS}	D16	Q7	D8
D	D28	D20	Q19	V_{SS}	V_{SS}	V_{SS}	V_{SS}	V_{SS}	Q16	D15	D7
E	Q29	D29	Q20	V_{DDQ}	V_{SS}	V_{SS}	V_{SS}	V_{DDQ}	Q15	D6	Q6
F	Q30	Q21	D21	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	D14	Q14	Q5
G	D30	D22	Q22	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	Q13	D13	D5
H	$\overline{\text{DOFF}}$	V_{REF}	V_{DDQ}	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	V_{DDQ}	V_{REF}	ZQ
J	D31	Q31	D23	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	D12	Q4	D4
K	Q32	D32	Q23	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	Q12	D3	Q3
L	Q33	Q24	D24	V_{DDQ}	V_{SS}	V_{SS}	V_{SS}	V_{DDQ}	D11	Q11	Q2
M	D33	Q34	D25	V_{SS}	V_{SS}	V_{SS}	V_{SS}	V_{SS}	D10	Q1	D2
N	D34	D26	Q25	V_{SS}	A	A	A	V_{SS}	Q10	D9	D1
P	Q35	D35	Q26	A	A	C	A	A	Q9	D0	Q0
R	TDO	TCK	A	A	A	$\overline{\text{C}}$	A	A	A	TMS	TDI

Note

1. NC/72M, NC/144M, and NC/288M are not connected to the die and can be tied to any voltage level.

Pin Definitions

Pin Name	I/O	Pin Description
D _[x:0]	Input-synchronous	Data input signals. Sampled on the rising edge of K and \bar{K} clocks during valid write operations. CY7C1423KV18 - D _[17:0] CY7C1424KV18 - D _[35:0]
\bar{LD}	Input-synchronous	Synchronous load. This input is brought LOW when a bus cycle sequence is defined. This definition includes address and read/write direction. All transactions operate on a burst of 2 data (one clock period of bus activity).
$\overline{BWS_0}$, $\overline{BWS_1}$, $\overline{BWS_2}$, $\overline{BWS_3}$	Input-synchronous	Byte write select 0, 1, 2, and 3 – active LOW. Sampled on the rising edge of the K and \bar{K} clocks during write operations. Used to select which byte is written into the device during the current portion of the write operations. Bytes not written remain unaltered. CY7C1423KV18 – $\overline{BWS_0}$ controls D _[8:0] , $\overline{BWS_1}$ controls D _[17:9] . CY7C1424KV18 – $\overline{BWS_0}$ controls D _[8:0] , $\overline{BWS_1}$ controls D _[17:9] , $\overline{BWS_2}$ controls D _[26:18] and $\overline{BWS_3}$ controls D _[35:27] . All the byte write selects are sampled on the same edge as the data. Deselecting a byte write select ignores the corresponding byte of data and it is not written into the device.
A	Input-synchronous	Address inputs. Sampled on the rising edge of the K clock during active read and write operations. These address inputs are multiplexed for both read and write operations. Internally, the device is organized as 2M × 18 (2 arrays each of 1M × 18) for CY7C1423KV18 and 1M × 36 (2 arrays each of 512K × 36) for CY7C1424KV18. Therefore, only 20 address inputs are needed to access the entire memory array of CY7C1423KV18 and 19 address inputs for CY7C1424KV18. These inputs are ignored when the appropriate port is deselected.
Q _[x:0]	Outputs-synchronous	Data output signals. These pins drive out the requested data during a read operation. Valid data is driven out on the rising edge of both the C and \bar{C} clocks during read operations, or K and \bar{K} when in single clock mode. When the read port is deselected, Q _[x:0] are automatically tristated. CY7C1423KV18 – Q _[17:0] CY7C1424KV18 – Q _[35:0]
R/ \bar{W}	Input-synchronous	Synchronous read/write input. When \bar{LD} is LOW, this input designates the access type (read when R/ \bar{W} is HIGH, write when R/ \bar{W} is LOW) for the loaded address. R/ \bar{W} must meet the setup and hold times around the edge of K.
C	Input clock	Positive input clock for output data. C is used in conjunction with \bar{C} to clock out the read data from the device. C and \bar{C} can be used together to deskew the flight times of various devices on the board back to the controller. See Application Example on page 8 for further details.
\bar{C}	Input clock	Negative input clock for output data. \bar{C} is used in conjunction with C to clock out the read data from the device. C and \bar{C} can be used together to deskew the flight times of various devices on the board back to the controller. See Application Example on page 8 for further details.
K	Input clock	Positive input clock input. The rising edge of K is used to capture synchronous inputs to the device and to drive out data through Q _[x:0] when in single clock mode. All accesses are initiated on the rising edge of K.
\bar{K}	Input clock	Negative input clock input. \bar{K} is used to capture synchronous inputs being presented to the device and to drive out data through Q _[x:0] when in single clock mode.
CQ	Echo clock	CQ referenced with respect to C. This is a free running clock and is synchronized to the input clock for output data (C) of the DDR II. In the single clock mode, CQ is generated with respect to K. The timings for the echo clocks is shown in the Switching Characteristics on page 23 .
\bar{CQ}	Echo clock	CQ referenced with respect to \bar{C}. This is a free running clock and is synchronized to the input clock for output data (\bar{C}) of the DDR II. In the single clock mode, \bar{CQ} is generated with respect to \bar{K} . The timings for the echo clocks is shown in the Switching Characteristics on page 23 .
ZQ	Input	Output impedance matching input. This input is used to tune the device outputs to the system data bus impedance. CQ, \bar{CQ} , and Q _[x:0] output impedance are set to 0.2 × RQ, where RQ is a resistor connected between ZQ and ground. Alternatively, this pin can be connected directly to V _{DDQ} , which enables the minimum impedance mode. This pin cannot be connected directly to GND or left unconnected.

Pin Definitions *(continued)*

Pin Name	I/O	Pin Description
DOFF	Input	PLL turn off – active LOW. Connecting this pin to ground turns off the PLL inside the device. The timing in the PLL turned off operation differs from those listed in this data sheet. For normal operation, this pin is connected to a pull-up through a 10 Kohm or less pull-up resistor. The device behaves in DDR I mode when the PLL is turned off. In this mode, the device can be operated at a frequency of up to 167 MHz with DDR I timing.
TDO	Output	TDO pin for JTAG.
TCK	Input	TCK pin for JTAG.
TDI	Input	TDI pin for JTAG.
TMS	Input	TMS pin for JTAG.
NC	N/A	Not connected to the die. Can be tied to any voltage level.
NC/72M	N/A	Not connected to the die. Can be tied to any voltage level.
NC/144M	N/A	Not connected to the die. Can be tied to any voltage level.
NC/288M	N/A	Not connected to the die. Can be tied to any voltage level.
V _{REF}	Input-reference	Reference voltage input. Static input used to set the reference level for HSTL inputs, outputs, and AC measurement points.
V _{DD}	Power supply	Power supply inputs to the core of the device.
V _{SS}	Ground	Ground for the device.
V _{DDQ}	Power supply	Power supply inputs for the outputs of the device.

Functional Overview

The CY7C1423KV18, and CY7C1424KV18 are synchronous pipelined burst SRAMs equipped with a DDR II separate I/O interface, which operates with a read latency of one and half cycles when DOFF pin is tied HIGH. When DOFF pin is set LOW or connected to V_{SS} the device behaves in DDR I mode with a read latency of one clock cycle.

Accesses are initiated on the rising edge of the positive input clock (K). All synchronous input timing is referenced from the rising edge of the input clocks (K and K) and all output timing is referenced to the rising edge of the output clocks (C/C, or K/K when in single clock mode).

All synchronous data inputs (D_[x:0]) pass through input registers controlled by the rising edge of the input clocks (K and K). All synchronous data outputs (Q_[x:0]) pass through output registers controlled by the rising edge of the output clocks (C/C, or K/K when in single-clock mode).

All synchronous control (R/W, LD, BWS_[0:X]) inputs pass through input registers controlled by the rising edge of the input clock (K).

CY7C1423KV18 is described in the following sections. The same basic descriptions apply to CY7C1424KV18.

Read Operations

The CY7C1423KV18 is organized internally as two arrays of 1 M × 18. Accesses are completed in a burst of two sequential 18-bit data words. Read operations are initiated by asserting R/W HIGH and LD LOW at the rising edge of the positive input clock (K). The address presented to address inputs is stored in the read address register. Following the next K clock rise the corresponding lowest order 18-bit word of data is driven onto the

Q_[17:0] using C as the output timing reference. On the subsequent rising edge of C, the next 18-bit data word is driven onto the Q_[17:0]. The requested data is valid 0.45 ns from the rising edge of the output clock (C or C, or K and K when in single clock mode, for 250 MHz device). Read accesses can be initiated on every rising edge of the positive input clock (K). This pipelines the data flow such that data is transferred out of the device on every rising edge of the output clocks, C/C (or K/K when in single clock mode).

The CY7C1423KV18 first completes the pending read transactions, when read access is deselected. Synchronous internal circuitry automatically tristates the output following the next rising edge of the positive output clock (C).

Write Operations

Write operations are initiated by asserting R/W LOW and LD LOW at the rising edge of the positive input clock (K). The address presented to address inputs is stored in the write address register. On the following K clock rise the data presented to D_[17:0] is latched and stored into the 18-bit write data register, provided BWS_[1:0] are both asserted active. On the subsequent rising edge of the negative input clock (K) the information presented to D_[17:0] is also stored into the write data register, provided BWS_[1:0] are both asserted active. The 36 bits of data are then written into the memory array at the specified location. Write accesses can be initiated on every rising edge of the positive input clock (K). This pipelines the data flow such that 18 bits of data can be transferred into the device on every rising edge of the input clocks (K and K).

When write access is deselected, the device ignores all inputs after the pending write operations are completed.

Byte Write Operations

Byte write operations are supported by the CY7C1423KV18. A write operation is initiated as described in [Write Operations on page 6](#). The bytes that are written are determined by \overline{BWS}_0 and \overline{BWS}_1 , which are sampled with each set of 18-bit data words. Asserting the appropriate byte write select input during the data portion of a write latches the data being presented and writes it into the device. Deasserting the byte write select input during the data portion of a write enables the data stored in the device for that byte to remain unaltered. This feature is used to simplify read, modify, and write operations to a byte write operation.

Single Clock Mode

The CY7C1423KV18 is used with a single clock that controls both the input and output registers. In this mode the device recognizes only a single pair of input clocks (K and \overline{K}) that control both the input and output registers. This operation is identical to the operation if the device had zero skew between the K/ \overline{K} and C/ \overline{C} clocks. All timing parameters remain the same in this mode. To use this mode of operation, tie C and \overline{C} HIGH at power on. This function is a strap option and not alterable during device operation.

DDR Operation

The CY7C1423KV18 enables high performance operation through high clock frequencies (achieved through pipelining) and double data rate mode of operation.

If a read occurs after a write cycle, address and data for the write are stored in registers. The write information must be stored because the SRAM cannot perform the last word write to the array without conflicting with the read. The data stays in this register until the next write cycle occurs. On the first write cycle after the read(s), the stored data from the earlier write is written into the SRAM array. This is called a posted write.

Depth Expansion

Depth expansion requires replicating the \overline{LD} control signal for each bank. All other control signals can be common between banks as appropriate.

Programmable Impedance

An external resistor, RQ, must be connected between the ZQ pin on the SRAM and V_{SS} to enable the SRAM to adjust its output driver impedance. The value of RQ must be $5 \times$ the value of the intended line impedance driven by the SRAM. The allowable range of RQ to guarantee impedance matching with a tolerance of $\pm 15\%$ is between 175Ω and 350Ω , with $V_{DDQ} = 1.5 \text{ V}$. The output impedance is adjusted every 1024 cycles at power up to account for drifts in supply voltage and temperature.

Echo Clocks

Echo clocks are provided on the DDR II to simplify data capture on high speed systems. Two echo clocks are generated by the DDR II. CQ is referenced with respect to C and \overline{CQ} is referenced with respect to \overline{C} . These are free running clocks and are synchronized to the output clock of the DDR II. In the single clock mode, CQ is generated with respect to K and \overline{CQ} is generated with respect to \overline{K} . The timing for the echo clocks is shown in [Switching Characteristics on page 23](#).

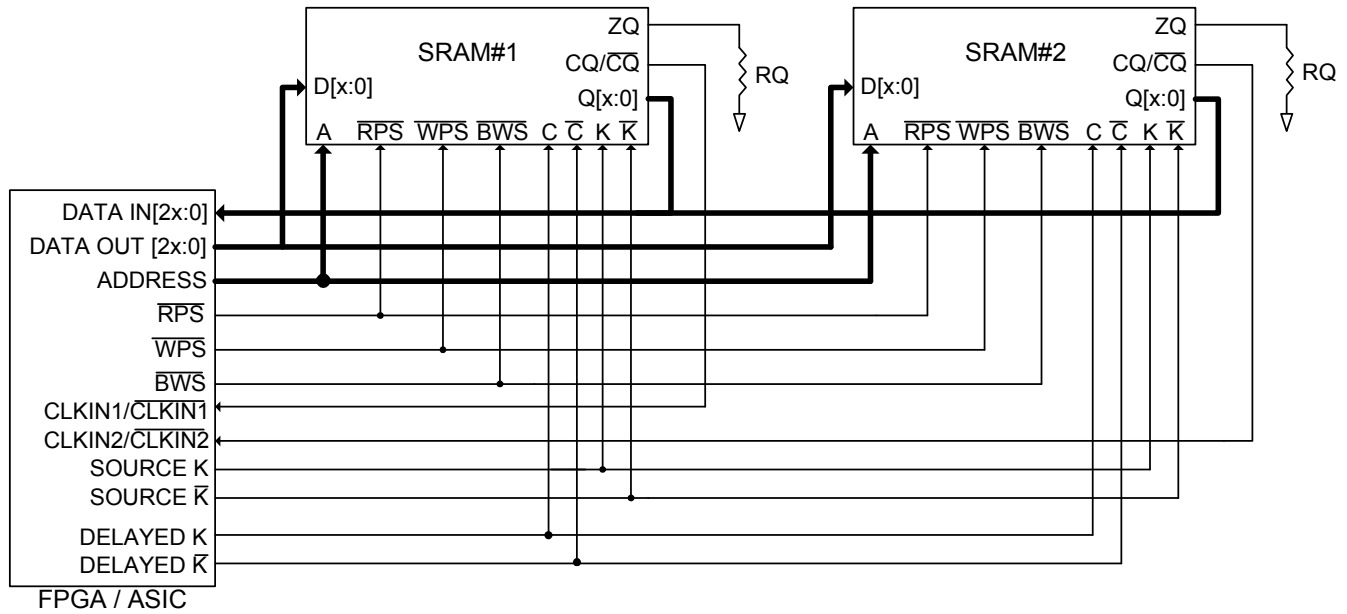
PLL

These chips use a phase locked loop (PLL) that is designed to function between 120 MHz and the specified maximum clock frequency. During power-up, when the \overline{DOFF} is tied HIGH, the PLL is locked after 20 μs of stable clock. The PLL can also be reset by slowing or stopping the input clocks K and \overline{K} for a minimum of 30 ns. However, it is not necessary to reset the PLL to lock it to the desired frequency. The PLL automatically locks 20 μs after a stable clock is presented. The PLL may be disabled by applying ground to the \overline{DOFF} pin. When the PLL is turned off, the device behaves in DDR I mode (with one cycle latency and a longer access time).

Application Example

Figure 2 shows four DDR II SIO used in an application.

Figure 2. Application Example (Width Expansion)



Truth Table

The truth table for CY7C1423KV18 and CY7C1424KV18 follows. [2, 3, 4, 5, 6, 7]

Operation	K	$\overline{\text{LD}}$	$\overline{\text{R/W}}$	DQ	DQ
Write cycle: Load address; wait one cycle; input write data on consecutive K and $\overline{\text{K}}$ rising edges.	L–H	L	L	D(A + 0) at K(t + 1)↑	D(A + 1) at $\overline{\text{K}}$ (t + 1)↑
Read cycle: Load address; wait one and a half cycle; read data on consecutive $\overline{\text{C}}$ and C rising edges.	L–H	L	H	Q(A + 0) at $\overline{\text{C}}$ (t + 1)↑	Q(A + 1) at C(t + 2)↑
NOP: No operation	L–H	H	X	High Z	High Z
Standby: Clock stopped	Stopped	X	X	Previous state	Previous state

Write Cycle Descriptions

The write cycle description table for CY7C1423KV18 follows. [2, 8]

$\overline{\text{BWS}}_0$	$\overline{\text{BWS}}_1$	K	$\overline{\text{K}}$	Comments
L	L	L–H	–	During the data portion of a write sequence: CY7C1423KV18 – both bytes (D _[17:0]) are written into the device.
L	L	–	L–H	During the data portion of a write sequence: CY7C1423KV18 – both bytes (D _[17:0]) are written into the device.
L	H	L–H	–	During the data portion of a write sequence: CY7C1423KV18 – only the lower byte (D _[8:0]) is written into the device, D _[17:9] remains unaltered.
L	H	–	L–H	During the data portion of a write sequence: CY7C1423KV18 – only the lower byte (D _[8:0]) is written into the device, D _[17:9] remains unaltered.
H	L	L–H	–	During the data portion of a write sequence: CY7C1423KV18 – only the upper byte (D _[17:9]) is written into the device, D _[8:0] remains unaltered.
H	L	–	L–H	During the data portion of a write sequence: CY7C1423KV18 – only the upper byte (D _[17:9]) is written into the device, D _[8:0] remains unaltered.
H	H	L–H	–	No data is written into the devices during this portion of a write operation.
H	H	–	L–H	No data is written into the devices during this portion of a write operation.

Notes

- X = "Don't Care," H = Logic HIGH, L = Logic LOW, ↑ represents rising edge.
- Device powers up deselected with the outputs in a tristate condition.
- "A" represents address location latched by the devices when transaction was initiated. A + 0, A + 1 represents the internal address sequence in the burst.
- "t" represents the cycle at which a read/write operation is started. t + 1, and t + 2 are the first, and second clock cycles respectively succeeding the "t" clock cycle.
- Data inputs are registered at K and $\overline{\text{K}}$ rising edges. Data outputs are delivered on C and $\overline{\text{C}}$ rising edges, except when in single clock mode.
- Ensure that when the clock is stopped K = K and C = C = HIGH. This is not essential, but permits most rapid restart by overcoming transmission line charging symmetrically.
- Is based on a write cycle that was initiated in accordance with the [Truth Table on page 9](#). $\overline{\text{BWS}}_0$, $\overline{\text{BWS}}_1$, $\overline{\text{BWS}}_2$, and $\overline{\text{BWS}}_3$ can be altered on different portions of a write cycle, as long as the setup and hold requirements are achieved.

Write Cycle Descriptions

The write cycle description table for CY7C1424KV18 follows. [9, 10]

$\overline{\text{BWS}}_0$	$\overline{\text{BWS}}_1$	$\overline{\text{BWS}}_2$	$\overline{\text{BWS}}_3$	K	$\overline{\text{K}}$	Comments
L	L	L	L	L-H	–	During the data portion of a write sequence, all four bytes ($D_{[35:0]}$) are written into the device.
L	L	L	L	–	L-H	During the data portion of a write sequence, all four bytes ($D_{[35:0]}$) are written into the device.
L	H	H	H	L-H	–	During the data portion of a write sequence, only the lower byte ($D_{[8:0]}$) is written into the device. $D_{[35:9]}$ remains unaltered.
L	H	H	H	–	L-H	During the data portion of a write sequence, only the lower byte ($D_{[8:0]}$) is written into the device. $D_{[35:9]}$ remains unaltered.
H	L	H	H	L-H	–	During the data portion of a write sequence, only the byte ($D_{[17:9]}$) is written into the device. $D_{[8:0]}$ and $D_{[35:18]}$ remains unaltered.
H	L	H	H	–	L-H	During the data portion of a write sequence, only the byte ($D_{[17:9]}$) is written into the device. $D_{[8:0]}$ and $D_{[35:18]}$ remains unaltered.
H	H	L	H	L-H	–	During the data portion of a write sequence, only the byte ($D_{[26:18]}$) is written into the device. $D_{[17:0]}$ and $D_{[35:27]}$ remains unaltered.
H	H	L	H	–	L-H	During the data portion of a write sequence, only the byte ($D_{[26:18]}$) is written into the device. $D_{[17:0]}$ and $D_{[35:27]}$ remains unaltered.
H	H	H	L	L-H	–	During the data portion of a write sequence, only the byte ($D_{[35:27]}$) is written into the device. $D_{[26:0]}$ remains unaltered.
H	H	H	L	–	L-H	During the data portion of a write sequence, only the byte ($D_{[35:27]}$) is written into the device. $D_{[26:0]}$ remains unaltered.
H	H	H	H	L-H	–	No data is written into the device during this portion of a write operation.
H	H	H	H	–	L-H	No data is written into the device during this portion of a write operation.

Notes

9. X = "Don't Care," H = Logic HIGH, L = Logic LOW, ↑ represents rising edge.

10. Is based on a write cycle that was initiated in accordance with the [Truth Table on page 9](#). $\overline{\text{BWS}}_0$, $\overline{\text{BWS}}_1$, $\overline{\text{BWS}}_2$, and $\overline{\text{BWS}}_3$ can be altered on different portions of a write cycle, as long as the setup and hold requirements are achieved.

IEEE 1149.1 Serial Boundary Scan (JTAG)

These SRAMs incorporate a serial boundary scan test access port (TAP) in the FBGA package. This part is fully compliant with IEEE Standard #1149.1-2001. The TAP operates using JEDEC standard 1.8 V IO logic levels.

Disabling the JTAG Feature

It is possible to operate the SRAM without using the JTAG feature. To disable the TAP controller, TCK must be tied LOW (V_{SS}) to prevent clocking of the device. TDI and TMS are internally pulled up and may be unconnected. They may alternatively be connected to V_{DD} through a pull-up resistor. TDO must be left unconnected. Upon power-up, the device comes up in a reset state, which does not interfere with the operation of the device.

Test Access Port

Test Clock

The test clock is used only with the TAP controller. All inputs are captured on the rising edge of TCK. All outputs are driven from the falling edge of TCK.

Test Mode Select (TMS)

The TMS input is used to give commands to the TAP controller and is sampled on the rising edge of TCK. This pin may be left unconnected if the TAP is not used. The pin is pulled up internally, resulting in a logic HIGH level.

Test Data-In (TDI)

The TDI pin is used to serially input information into the registers and can be connected to the input of any of the registers. The register between TDI and TDO is chosen by the instruction that is loaded into the TAP instruction register. For information about loading the instruction register, see the [TAP Controller State Diagram on page 13](#). TDI is internally pulled up and can be unconnected if the TAP is unused in an application. TDI is connected to the most significant bit (MSB) on any register.

Test Data-Out (TDO)

The TDO output pin is used to serially clock data out from the registers. The output is active, depending upon the current state of the TAP state machine (see [Instruction Codes on page 17](#)). The output changes on the falling edge of TCK. TDO is connected to the least significant bit (LSB) of any register.

Performing a TAP Reset

A reset is performed by forcing TMS HIGH (V_{DD}) for five rising edges of TCK. This reset does not affect the operation of the SRAM and is performed when the SRAM is operating. At power-up, the TAP is reset internally to ensure that TDO comes up in a high Z state.

TAP Registers

Registers are connected between the TDI and TDO pins to scan the data in and out of the SRAM test circuitry. Only one register can be selected at a time through the instruction registers. Data is serially loaded into the TDI pin on the rising edge of TCK. Data is output on the TDO pin on the falling edge of TCK.

Instruction Register

Three-bit instructions are serially loaded into the instruction register. This register is loaded when it is placed between the TDI and TDO pins, as shown in [TAP Controller Block Diagram on page 14](#). Upon power-up, the instruction register is loaded with the IDCODE instruction. It is also loaded with the IDCODE instruction if the controller is placed in a reset state, as described in the previous section.

When the TAP controller is in the Capture-IR state, the two least significant bits are loaded with a binary "01" pattern to enable fault isolation of the board level serial test path.

Bypass Register

To save time when serially shifting data through registers, it is sometimes advantageous to skip certain chips. The bypass register is a single-bit register that can be placed between TDI and TDO pins. This enables shifting of data through the SRAM with minimal delay. The bypass register is set LOW (V_{SS}) when the BYPASS instruction is executed.

Boundary Scan Register

The boundary scan register is connected to all of the input and output pins on the SRAM. Several No Connect (NC) pins are also included in the scan register to reserve pins for higher density devices.

The boundary scan register is loaded with the contents of the RAM input and output ring when the TAP controller is in the Capture-DR state and is then placed between the TDI and TDO pins when the controller is moved to the Shift-DR state. The EXTEST, SAMPLE/PRELOAD, and SAMPLE Z instructions are used to capture the contents of the input and output ring.

The [Boundary Scan Order on page 18](#) shows the order in which the bits are connected. Each bit corresponds to one of the bumps on the SRAM package. The MSB of the register is connected to TDI, and the LSB is connected to TDO.

Identification (ID) Register

The ID register is loaded with a vendor-specific, 32-bit code during the Capture-DR state when the IDCODE command is loaded in the instruction register. The IDCODE is hardwired into the SRAM and is shifted out when the TAP controller is in the Shift-DR state. The ID register has a vendor code and other information described in [Identification Register Definitions on page 17](#).

TAP Instruction Set

Eight different instructions are possible with the three-bit instruction register. All combinations are listed in [Instruction Codes on page 17](#). Three of these instructions are listed as RESERVED and must not be used. The other five instructions are described in this section in detail.

Instructions are loaded into the TAP controller during the Shift-IR state when the instruction register is placed between TDI and TDO. During this state, instructions are shifted through the instruction register through the TDI and TDO pins. To execute the instruction after it is shifted in, the TAP controller must be moved into the Update-IR state.

IDCODE

The IDCODE instruction loads a vendor-specific, 32-bit code into the instruction register. It also places the instruction register between the TDI and TDO pins and shifts the IDCODE out of the device when the TAP controller enters the Shift-DR state. The IDCODE instruction is loaded into the instruction register at power up or whenever the TAP controller is supplied a Test-Logic-Reset state.

SAMPLE Z

The SAMPLE Z instruction connects the boundary scan register between the TDI and TDO pins when the TAP controller is in a Shift-DR state. The SAMPLE Z command puts the output bus into a high Z state until the next command is supplied during the Update IR state.

SAMPLE/PRELOAD

SAMPLE/PRELOAD is a 1149.1 mandatory instruction. When the SAMPLE/PRELOAD instructions are loaded into the instruction register and the TAP controller is in the Capture-DR state, a snapshot of data on the input and output pins is captured in the boundary scan register.

The user must be aware that the TAP controller clock can only operate at a frequency up to 20 MHz, while the SRAM clock operates more than an order of magnitude faster. Because there is a large difference in the clock frequencies, it is possible that during the Capture-DR state, an input or output undergoes a transition. The TAP may then try to capture a signal while in transition (metastable state). This does not harm the device, but there is no guarantee as to the value that is captured. Repeatable results may not be possible.

To guarantee that the boundary scan register captures the correct value of a signal, the SRAM signal must be stabilized long enough to meet the TAP controller's capture setup plus hold times (t_{CS} and t_{CH}). The SRAM clock input might not be captured correctly if there is no way in a design to stop (or slow) the clock during a SAMPLE/PRELOAD instruction. If this is an issue, it is still possible to capture all other signals and simply ignore the value of the CK and \overline{CK} captured in the boundary scan register.

After the data is captured, it is possible to shift out the data by putting the TAP into the Shift-DR state. This places the boundary scan register between the TDI and TDO pins.

PRELOAD places an initial data pattern at the latched parallel outputs of the boundary scan register cells before the selection of another boundary scan test operation.

The shifting of data for the SAMPLE and PRELOAD phases can occur concurrently when required, that is, while the data captured is shifted out, the preloaded data can be shifted in.

BYPASS

When the BYPASS instruction is loaded in the instruction register and the TAP is placed in a Shift-DR state, the bypass register is placed between the TDI and TDO pins. The advantage of the BYPASS instruction is that it shortens the boundary scan path when multiple devices are connected together on a board.

EXTEST

The EXTEST instruction drives the preloaded data out through the system output pins. This instruction also connects the boundary scan register for serial access between the TDI and TDO in the Shift-DR controller state.

EXTEST OUTPUT BUS TRISTATE

IEEE Standard 1149.1 mandates that the TAP controller be able to put the output bus into a tristate mode.

The boundary scan register has a special bit located at bit #108. When this scan cell, called the "extest output bus tristate," is latched into the preload register during the Update-DR state in the TAP controller, it directly controls the state of the output (Q-bus) pins, when the EXTEST is entered as the current instruction. When HIGH, it enables the output buffers to drive the output bus. When LOW, this bit places the output bus into a high Z condition.

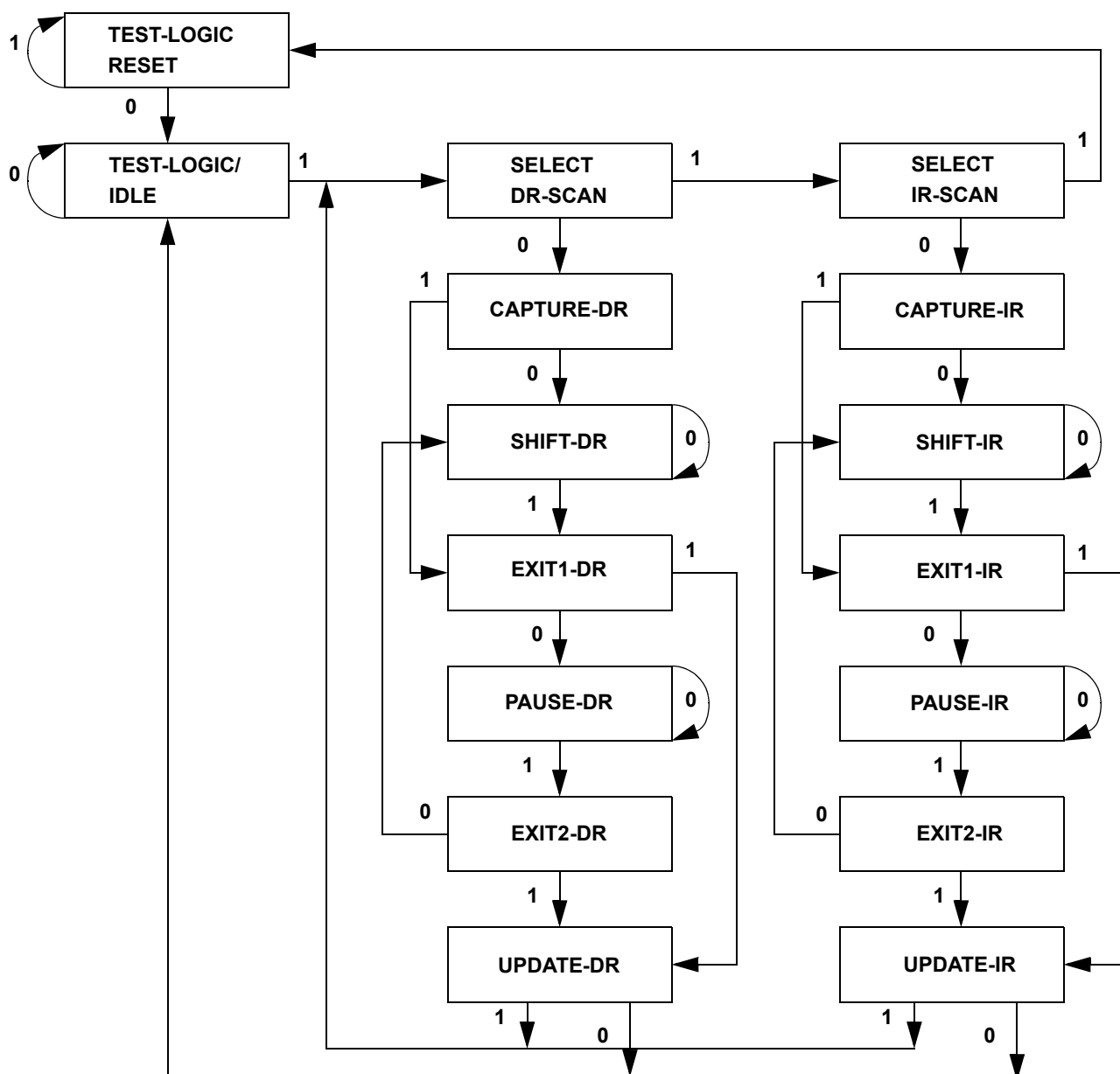
This bit is set by entering the SAMPLE/PRELOAD or EXTEST command, and then shifting the desired bit into that cell, during the Shift-DR state. During Update-DR, the value loaded into that shift-register cell latches into the preload register. When the EXTEST instruction is entered, this bit directly controls the output Q-bus pins. Note that this bit is pre-set LOW to enable the output when the device is powered up, and also when the TAP controller is in the Test-Logic-Reset state.

Reserved

These instructions are not implemented but are reserved for future use. Do not use these instructions.

TAP Controller State Diagram

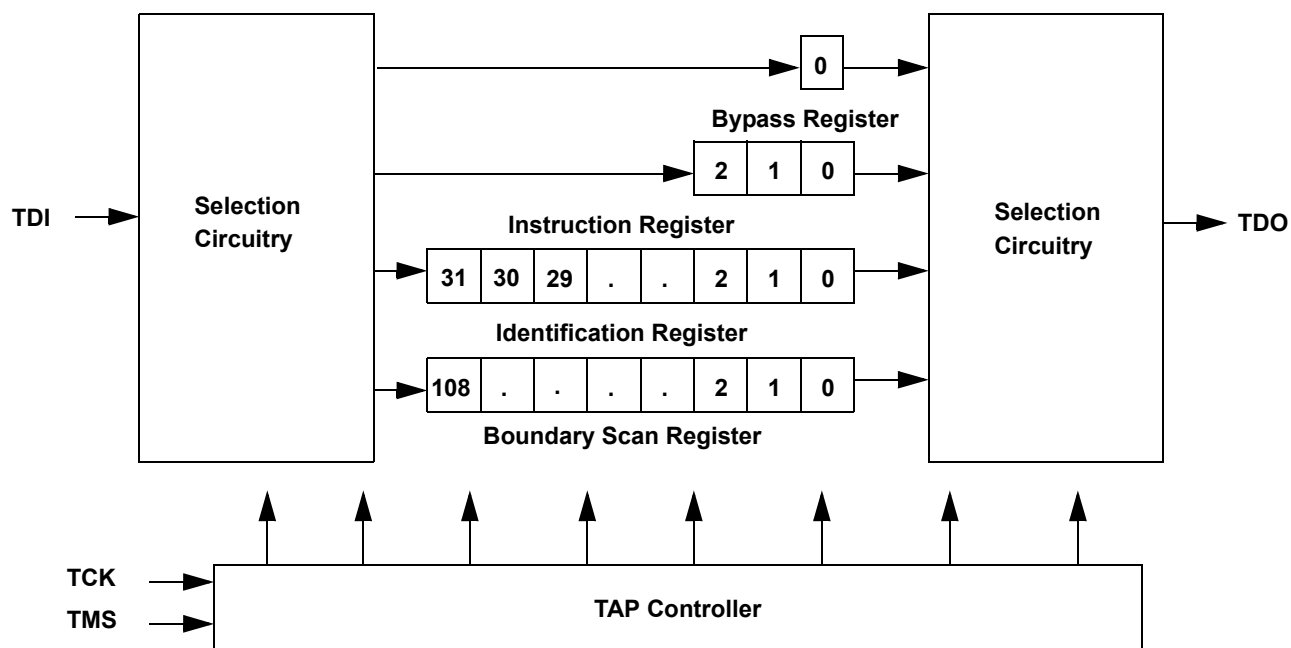
The state diagram for the TAP controller follows. ^[11]



Note

11. The 0/1 next to each state represents the value at TMS at the rising edge of TCK.

TAP Controller Block Diagram



TAP Electrical Characteristics

Over the Operating Range

Parameter [12, 13, 14]	Description	Test Conditions	Min	Max	Unit
V_{OH1}	Output HIGH voltage	$I_{OH} = -2.0 \text{ mA}$	1.4	–	V
V_{OH2}	Output HIGH voltage	$I_{OH} = -100 \text{ } \mu\text{A}$	1.6	–	V
V_{OL1}	Output LOW voltage	$I_{OL} = 2.0 \text{ mA}$	–	0.4	V
V_{OL2}	Output LOW voltage	$I_{OL} = 100 \text{ } \mu\text{A}$	–	0.2	V
V_{IH}	Input HIGH voltage		$0.65 \times V_{DD}$	$V_{DD} + 0.3$	V
V_{IL}	Input LOW voltage		–0.3	$0.35 \times V_{DD}$	V
I_X	Input and output load current	$GND \leq V_I \leq V_{DD}$	–5	5	μA

Notes

12. These characteristics pertain to the TAP inputs (TMS, TCK, TDI and TDO). Parallel load levels are specified in the [Electrical Characteristics on page 20](#).

13. Overshoot: $V_{IH(AC)} < V_{DDQ} + 0.85 \text{ V}$ (Pulse width less than $t_{CYC}/2$). Undershoot: $V_{IL(AC)} > -1.5 \text{ V}$ (Pulse width less than $t_{CYC}/2$).

14. All voltage referenced to ground.

TAP AC Switching Characteristics

Over the Operating Range

Parameter ^[15, 16]	Description	Min	Max	Unit
t_{TCYC}	TCK clock cycle time	50	–	ns
t_{TF}	TCK clock frequency	–	20	MHz
t_{TH}	TCK clock HIGH	20	–	ns
t_{TL}	TCK clock LOW	20	–	ns
Setup Times				
t_{TMSS}	TMS set-up to TCK clock rise	5	–	ns
t_{TDIS}	TDI set-up to TCK clock rise	5	–	ns
t_{CS}	Capture set-up to TCK rise	5	–	ns
Hold Times				
t_{TMSH}	TMS hold after TCK clock rise	5	–	ns
t_{TDIH}	TDI hold after clock rise	5	–	ns
t_{CH}	Capture hold after clock rise	5	–	ns
Output Times				
t_{TDOV}	TCK clock LOW to TDO valid	–	10	ns
t_{TDOX}	TCK clock LOW to TDO invalid	0	–	ns

Notes

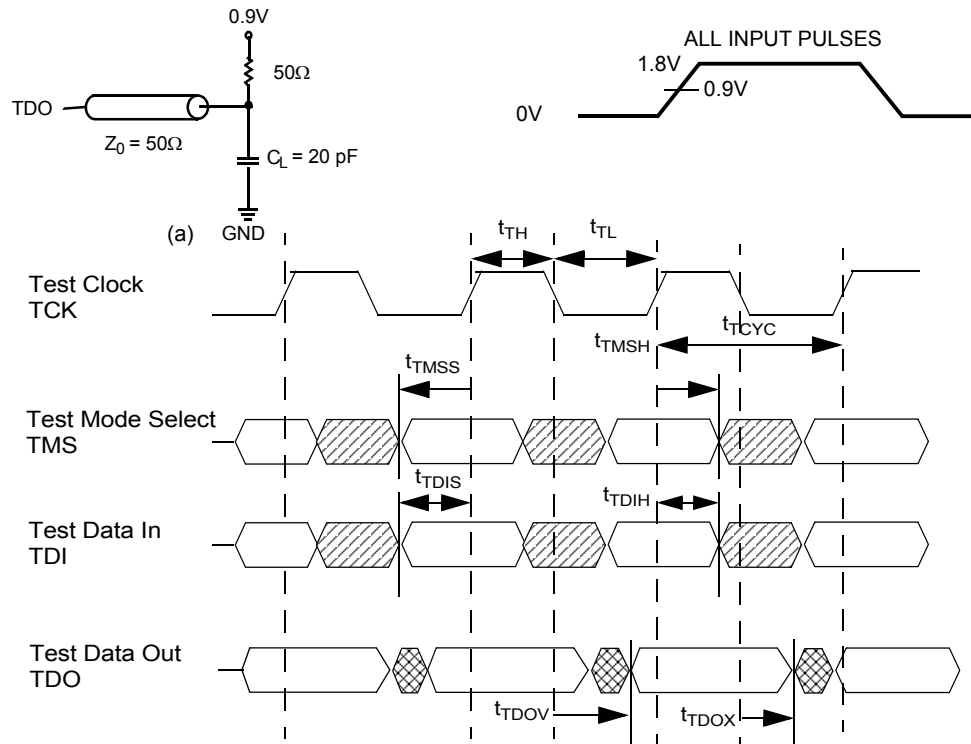
15. t_{CS} and t_{CH} refer to the setup and hold time requirements of latching data from the boundary scan register.

16. Test conditions are specified using the load in TAP AC Test Conditions. $t_R/t_F = 1$ ns.

TAP Timing and Test Conditions

Figure 3 shows the TAP timing and test conditions. [17]

Figure 3. TAP Timing and Test Conditions



Note

17. Test conditions are specified using the load in TAP AC Test Conditions. $t_R/t_F = 1$ ns.

Identification Register Definitions

Instruction Field	Value		Description
	CY7C1423KV18	CY7C1424KV18	
Revision number (31:29)	000	000	Version number.
Cypress device ID (28:12)	11010100010010111	11010100010100111	Defines the type of SRAM.
Cypress JEDEC ID (11:1)	00000110100	00000110100	Allows unique identification of SRAM vendor.
ID register presence (0)	1	1	Indicates the presence of an ID register.

Scan Register Sizes

Register Name	Bit Size
Instruction	3
Bypass	1
ID	32
Boundary scan	109

Instruction Codes

Instruction	Code	Description
EXTEST	000	Captures the input and output ring contents.
IDCODE	001	Loads the ID register with the vendor ID code and places the register between TDI and TDO. This operation does not affect SRAM operation.
SAMPLE Z	010	Captures the input and output contents. Places the boundary scan register between TDI and TDO. Forces all SRAM output drivers to a high Z state.
RESERVED	011	Do Not Use: This instruction is reserved for future use.
SAMPLE/PRELOAD	100	Captures the input and output ring contents. Places the boundary scan register between TDI and TDO. Does not affect the SRAM operation.
RESERVED	101	Do Not Use: This instruction is reserved for future use.
RESERVED	110	Do Not Use: This instruction is reserved for future use.
BYPASS	111	Places the bypass register between TDI and TDO. This operation does not affect SRAM operation.

Boundary Scan Order

Bit #	Bump ID	Bit #	Bump ID	Bit #	Bump ID	Bit #	Bump ID
0	6R	28	10G	56	6A	84	1J
1	6P	29	9G	57	5B	85	2J
2	6N	30	11F	58	5A	86	3K
3	7P	31	11G	59	4A	87	3J
4	7N	32	9F	60	5C	88	2K
5	7R	33	10F	61	4B	89	1K
6	8R	34	11E	62	3A	90	2L
7	8P	35	10E	63	2A	91	3L
8	9R	36	10D	64	1A	92	1M
9	11P	37	9E	65	2B	93	1L
10	10P	38	10C	66	3B	94	3N
11	10N	39	11D	67	1C	95	3M
12	9P	40	9C	68	1B	96	1N
13	10M	41	9D	69	3D	97	2M
14	11N	42	11B	70	3C	98	3P
15	9M	43	11C	71	1D	99	2N
16	9N	44	9B	72	2C	100	2P
17	11L	45	10B	73	3E	101	1P
18	11M	46	11A	74	2D	102	3R
19	9L	47	10A	75	2E	103	4R
20	10L	48	9A	76	1E	104	4P
21	11K	49	8B	77	2F	105	5P
22	10K	50	7C	78	3F	106	5N
23	9J	51	6C	79	1G	107	5R
24	9K	52	8A	80	1F	108	Internal
25	10J	53	7A	81	3G		
26	11J	54	7B	82	2G		
27	11H	55	6B	83	1H		

Power Up Sequence in DDR II SRAM

DDR II SRAMs must be powered up and initialized in a predefined manner to prevent undefined operations.

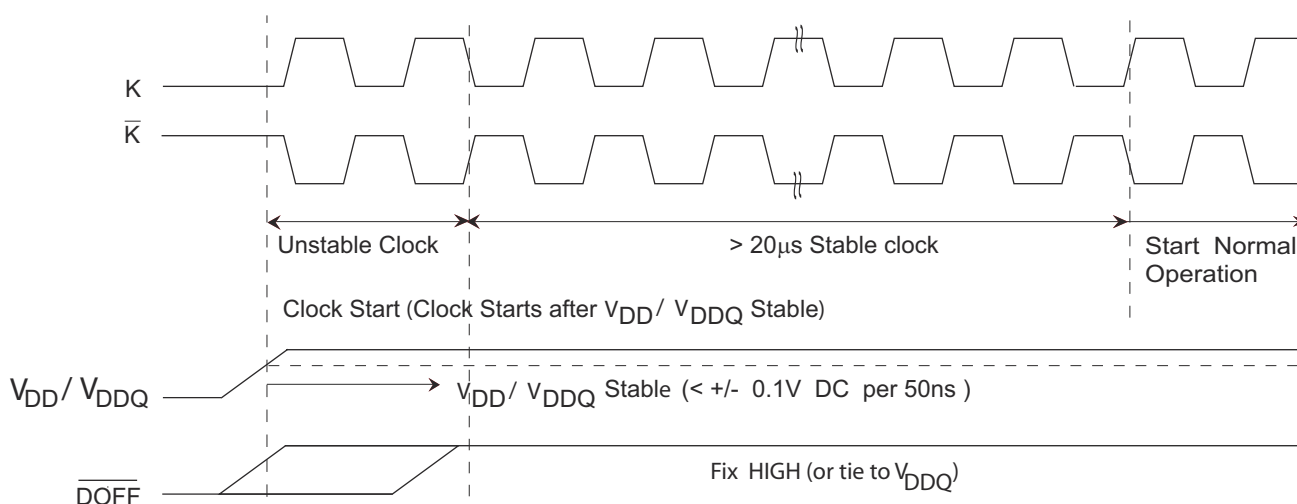
Power Up Sequence

- Apply power and drive $\overline{\text{DOFF}}$ either HIGH or LOW (All other inputs can be HIGH or LOW).
 - Apply V_{DD} before V_{DDQ} .
 - Apply V_{DDQ} before V_{REF} or at the same time as V_{REF} .
 - Drive $\overline{\text{DOFF}}$ HIGH.
- Provide stable $\overline{\text{DOFF}}$ (HIGH), power and clock (K, \bar{K}) for 20 μs to lock the PLL.

PLL Constraints

- PLL uses K clock as its synchronizing input. The input must have low phase jitter, which is specified as $t_{\text{KC Var}}$.
- The PLL functions at frequencies down to 120 MHz.
- If the input clock is unstable and the PLL is enabled, then the PLL may lock onto an incorrect frequency, causing unstable SRAM behavior. To avoid this, provide 20 μs of stable clock to relock to the desired clock frequency.

Figure 4. Power Up Waveforms



Maximum Ratings

Exceeding maximum ratings may impair the useful life of the device. These user guidelines are not tested.

Storage temperature -65 °C to +150 °C

Ambient temperature
with power applied -55 °C to +125 °C

Supply voltage on V_{DD} relative to GND -0.5 V to +2.9 V

Supply voltage on V_{DDQ} relative to GND -0.5 V to + V_{DD}

DC applied to outputs in high Z -0.5 V to $V_{DDQ} + 0.3$ V

DC input voltage ^[18] -0.5 V to $V_{DD} + 0.3$ V

Current into outputs (LOW) 20 mA

Static discharge voltage
(MIL-STD-883, M. 3015) > 2001 V

Latch-up current > 200 mA

Operating Range

Range	Ambient Temperature (T_A)	V_{DD} ^[19]	V_{DDQ} ^[19]
Commercial	0 °C to +70 °C	1.8 ± 0.1 V	1.4 V to V_{DD}

Neutron Soft Error Immunity

Parameter	Description	Test Conditions	Typ	Max*	Unit
LSBU	Logical single-bit upsets	25 °C	197	216	FIT/Mb
LMBU	Logical multi-bit upsets	25 °C	0	0.01	FIT/Mb
SEL	Single event latch-up	85 °C	0	0.1	FIT/Dev

* No LMBU or SEL events occurred during testing; this column represents a statistical χ^2 , 95% confidence limit calculation. For more details refer to Application Note AN54908 "Accelerated Neutron SER Testing and Calculation of Terrestrial Failure Rates".

Electrical Characteristics

Over the Operating Range

DC Electrical Characteristics

Over the Operating Range

Parameter ^[20]	Description	Test Conditions	Min	Typ	Max	Unit
V_{DD}	Power supply voltage		1.7	1.8	1.9	V
V_{DDQ}	IO supply voltage		1.4	1.5	V_{DD}	V
V_{OH}	Output HIGH voltage	Note 21	$V_{DDQ}/2 - 0.12$	–	$V_{DDQ}/2 + 0.12$	V
V_{OL}	Output LOW voltage	Note 22	$V_{DDQ}/2 - 0.12$	–	$V_{DDQ}/2 + 0.12$	V
$V_{OH(LOW)}$	Output HIGH voltage	$I_{OH} = -0.1$ mA, nominal impedance	$V_{DDQ} - 0.2$	–	V_{DDQ}	V
$V_{OL(LOW)}$	Output LOW voltage	$I_{OL} = 0.1$ mA, nominal impedance	V_{SS}	–	0.2	V
V_{IH}	Input HIGH voltage		$V_{REF} + 0.1$	–	$V_{DDQ} + 0.3$	V
V_{IL}	Input LOW voltage		-0.3	–	$V_{REF} - 0.1$	V
I_X	Input leakage current	$GND \leq V_I \leq V_{DDQ}$	-5	–	5	μ A
I_{OZ}	Output leakage current	$GND \leq V_I \leq V_{DDQ}$, output disabled	-5	–	5	μ A
V_{REF}	Input reference voltage ^[23]	Typical Value = 0.75 V	0.68	0.75	0.95	V

Notes

18. Overshoot: $V_{IH(AC)} < V_{DDQ} + 0.85$ V (Pulse width less than $t_{CYC}/2$), Undershoot: $V_{IL(AC)} > -1.5$ V (Pulse width less than $t_{CYC}/2$).

19. Power-up: assumes a linear ramp from 0 V to $V_{DD(min)}$ within 200 ms. During this time $V_{IH} < V_{DD}$ and $V_{DDQ} \leq V_{DD}$.

20. All voltage referenced to ground.

21. Outputs are impedance controlled. $I_{OH} = -(V_{DDQ}/2)/(RQ/5)$ for values of $175 \Omega \leq RQ \leq 350 \Omega$.

22. Outputs are impedance controlled. $I_{OL} = (V_{DDQ}/2)/(RQ/5)$ for values of $175 \Omega \leq RQ \leq 350 \Omega$.

23. $V_{REF(min)} = 0.68$ V or $0.46 V_{DDQ}$, whichever is larger, $V_{REF(max)} = 0.95$ V or $0.54 V_{DDQ}$, whichever is smaller.

Electrical Characteristics *(continued)*

Over the Operating Range

DC Electrical Characteristics *(continued)*

Over the Operating Range

Parameter ^[20]	Description	Test Conditions			Min	Typ	Max	Unit	
I _{DD} ^[24]	V _{DD} operating supply	V _{DD} = Max, I _{OUT} = 0 mA, f = f _{MAX} = 1/t _{CYC}	333 MHz	(× 18)	–	–	490	mA	
				(× 36)	–	–	600		
			300 MHz	(× 18)	–	–	460	mA	
				250 MHz	(× 18)	–	–		430
					(× 36)	–	–		490
I _{SB1}	Automatic power-down current	Max V _{DD} , both ports deselected, V _{IN} ≥ V _{IH} or V _{IN} ≤ V _{IL} , f = f _{MAX} = 1/t _{CYC} , inputs static	333 MHz	(× 18)	–	–	280	mA	
				(× 36)	–	–	280		
			300 MHz	(× 18)	–	–	270	mA	
				250 MHz	(× 18)	–	–		260
					(× 36)	–	–		260

Note

24. The operation current is calculated with 50% read cycle and 50% write cycle.

AC Electrical Characteristics

Over the Operating Range

Parameter ^[25]	Description	Test Conditions	Min	Typ	Max	Unit
V_{IH}	Input HIGH voltage		$V_{REF} + 0.2$	–	–	V
V_{IL}	Input LOW voltage		–	–	$V_{REF} - 0.2$	V

Capacitance

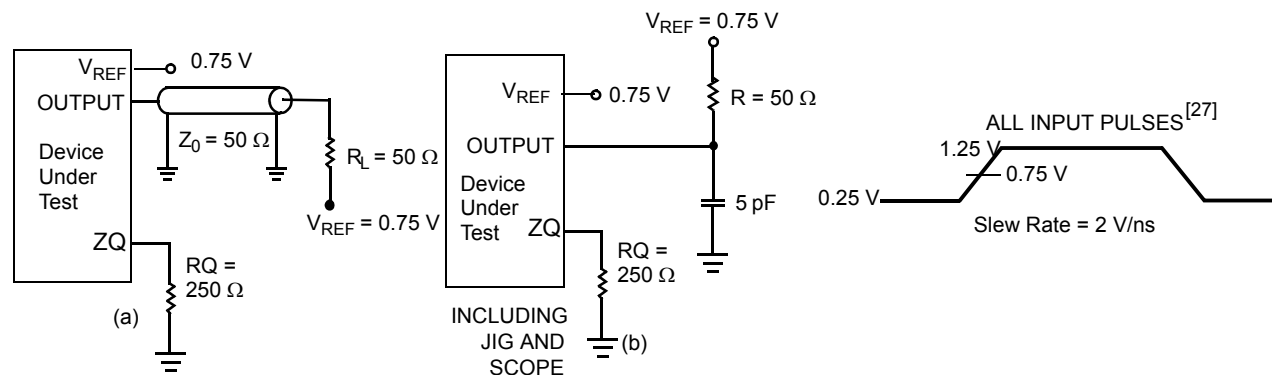
Parameter ^[26]	Description	Test Conditions	Max	Unit
C_{IN}	Input capacitance	$T_A = 25^\circ\text{C}$, $f = 1\text{ MHz}$, $V_{DD} = 1.8\text{ V}$, $V_{DDQ} = 1.5\text{ V}$	4	pF
C_O	Output capacitance		4	pF

Thermal Resistance

Parameter ^[26]	Description	Test Conditions	165-ball FBGA Package	Unit
Θ_{JA} (0 m/s)	Thermal resistance (junction to ambient)	Socketed on a $170 \times 220 \times 2.35\text{ mm}$, eight-layer printed circuit board	16.72	$^\circ\text{C/W}$
Θ_{JA} (1 m/s)			15.67	$^\circ\text{C/W}$
Θ_{JA} (3 m/s)			14.92	$^\circ\text{C/W}$
Θ_{JB}	Thermal resistance (junction to board)		13.67	$^\circ\text{C/W}$
Θ_{JC}	Thermal resistance (junction to case)		4.54	$^\circ\text{C/W}$

AC Test Loads and Waveforms

Figure 5. AC Test Loads and Waveforms



Notes

25. Overshoot: $V_{IH(AC)} < V_{DDQ} + 0.85\text{ V}$ (Pulse width less than $t_{CYC}/2$). Undershoot: $V_{IL(AC)} > -1.5\text{ V}$ (Pulse width less than $t_{CYC}/2$).

26. Tested initially and after any design or process change that may affect these parameters.

27. Unless otherwise noted, test conditions are based on signal transition time of 2 V/ns , timing reference levels of 0.75 V , $V_{ref} = 0.75\text{ V}$, $R_Q = 250\ \Omega$, $V_{DDQ} = 1.5\text{ V}$, input pulse levels of 0.25 V to 1.25 V , and output loading of the specified I_{OL}/I_{OH} and load capacitance shown in (a) of Figure 5.

Switching Characteristics

Over the Operating Range

Parameters [28, 29]		Description	333 MHz		300 MHz		250 MHz		Unit
Cypress Parameter	Consortium Parameter		Min	Max	Min	Max	Min	Max	
t _{POWER}		V _{DD} (typical) to the first access [30]	1	–	1	–	1	–	ms
t _{CYC}	t _{KHKH}	K clock and C clock cycle time	3.0	8.4	3.3	8.4	4.0	8.4	ns
t _{KH}	t _{KHKL}	Input clock (K/ \bar{K} ; C/ \bar{C}) HIGH	1.20	–	1.32	–	1.6	–	ns
t _{KL}	t _{KLKH}	Input clock (K/ \bar{K} ; C/ \bar{C}) LOW	1.20	–	1.32	–	1.6	–	ns
t _{KH\bar{K}H}	t _{KH\bar{K}H}	K clock rise to \bar{K} clock rise and C to \bar{C} rise (rising edge to rising edge)	1.35	–	1.49	–	1.8	–	ns
t _{KHCH}	t _{KHCH}	K/ \bar{K} clock rise to C/ \bar{C} clock rise (rising edge to rising edge)	0	1.30	0	1.45	0	1.8	ns
Setup Times									
t _{SA}	t _{AVKH}	Address set-up to K clock rise	0.4	–	0.4	–	0.5	–	ns
t _{SC}	t _{IVKH}	Control set-up to K clock rise (\bar{LD} , R/W)	0.4	–	0.4	–	0.5	–	ns
t _{SCDDR}	t _{IVKH}	Double data rate control set-up to clock (K/ \bar{K}) rise (BWS ₀ , BWS ₁ , BWS ₂ , BWS ₃)	0.3	–	0.3	–	0.35	–	ns
t _{SD}	t _{DVKH}	D _[X:0] set-up to clock (K/ \bar{K}) rise	0.3	–	0.3	–	0.35	–	ns
Hold Times									
t _{HA}	t _{KHAX}	Address hold after K clock rise	0.4	–	0.4	–	0.5	–	ns
t _{HC}	t _{KHIX}	Control hold after K clock rise (\bar{LD} , R/W)	0.4	–	0.4	–	0.5	–	ns
t _{HCDDR}	t _{KHIX}	Double data rate control hold after clock (K/ \bar{K}) rise (BWS ₀ , BWS ₁ , BWS ₂ , BWS ₃)	0.3	–	0.3	–	0.35	–	ns
t _{HD}	t _{KHDX}	D _[X:0] hold after clock (K/ \bar{K}) rise	0.3	–	0.3	–	0.35	–	ns

Notes

28. Unless otherwise noted, test conditions are based on signal transition time of 2 V/ns, timing reference levels of 0.75 V, V_{ref} = 0.75 V, R_Q = 250 Ω , V_{DDQ} = 1.5 V, input pulse levels of 0.25 V to 1.25 V, and output loading of the specified I_{OL}/I_{OH} and load capacitance shown in (a) of Figure 5 on page 22.

29. When a part with a maximum frequency above 167 MHz is operating at a lower clock frequency, it requires the input timings of the frequency range in which it is operated and outputs data with the output timings of that frequency range.

30. This part has a voltage regulator internally; t_{POWER} is the time that the power must be supplied above V_{DD(minimum)} initially before a read or write operation can be initiated.

Switching Characteristics *(continued)*

Over the Operating Range

Parameters ^[28, 29]		Description	333 MHz		300 MHz		250 MHz		Unit
Cypress Parameter	Consortium Parameter		Min	Max	Min	Max	Min	Max	
Output Times									
t _{CO}	t _{CHQV}	C/ \overline{C} clock rise (or K/ \overline{K} in single clock mode) to data valid	–	0.45	–	0.45	–	0.45	ns
t _{DOH}	t _{CHQX}	Data output hold after output C/ \overline{C} clock rise (active to active)	–0.45	–	–0.45	–	–0.45	–	ns
t _{CCQO}	t _{CHCQV}	C/ \overline{C} clock rise to echo clock valid	–	0.45	–	0.45	–	0.45	ns
t _{CQOH}	t _{CHCQX}	Echo clock hold after C/ \overline{C} clock rise	–0.45	–	–0.45	–	–0.45	–	ns
t _{CQD}	t _{CQHCV}	Echo clock high to data valid	–	0.25	–	0.27	–	0.30	ns
t _{CQDOH}	t _{CQHCVX}	Echo clock high to data invalid	–0.25	–	–0.27	–	–0.30	–	ns
t _{CQH}	t _{CQHCQL}	Output clock (CQ/ \overline{CQ}) HIGH ^[31]	1.25	–	1.40	–	1.75	–	ns
t _{CQH\overline{CQ}}	t _{CQH\overline{CQ}}	CQ clock rise to \overline{CQ} clock rise (rising edge to rising edge) ^[31]	1.25	–	1.40	–	1.75	–	ns
t _{CHZ}	t _{CHQZ}	Clock (C/ \overline{C}) rise to high Z (active to high Z) ^[32, 33]	–	0.45	–	0.45	–	0.45	ns
t _{CLZ}	t _{CHQX1}	Clock (C/ \overline{C}) rise to low Z ^[32, 33]	–0.45	–	–0.45	–	–0.45	–	ns
PLL Timing									
t _{KC Var}	t _{KC Var}	Clock phase jitter	–	0.20	–	0.20	–	0.20	ns
t _{KC lock}	t _{KC lock}	PLL lock time (K, C) ^[34]	20	–	20	–	20	–	μs
t _{KC Reset}	t _{KC Reset}	K static to PLL reset	30	–	30	–	30	–	ns

Notes

31. These parameters are extrapolated from the input timing parameters ($t_{CYC}/2 - 250$ ps, where 250 ps is the internal jitter). These parameters are only guaranteed by design and are not tested in production.

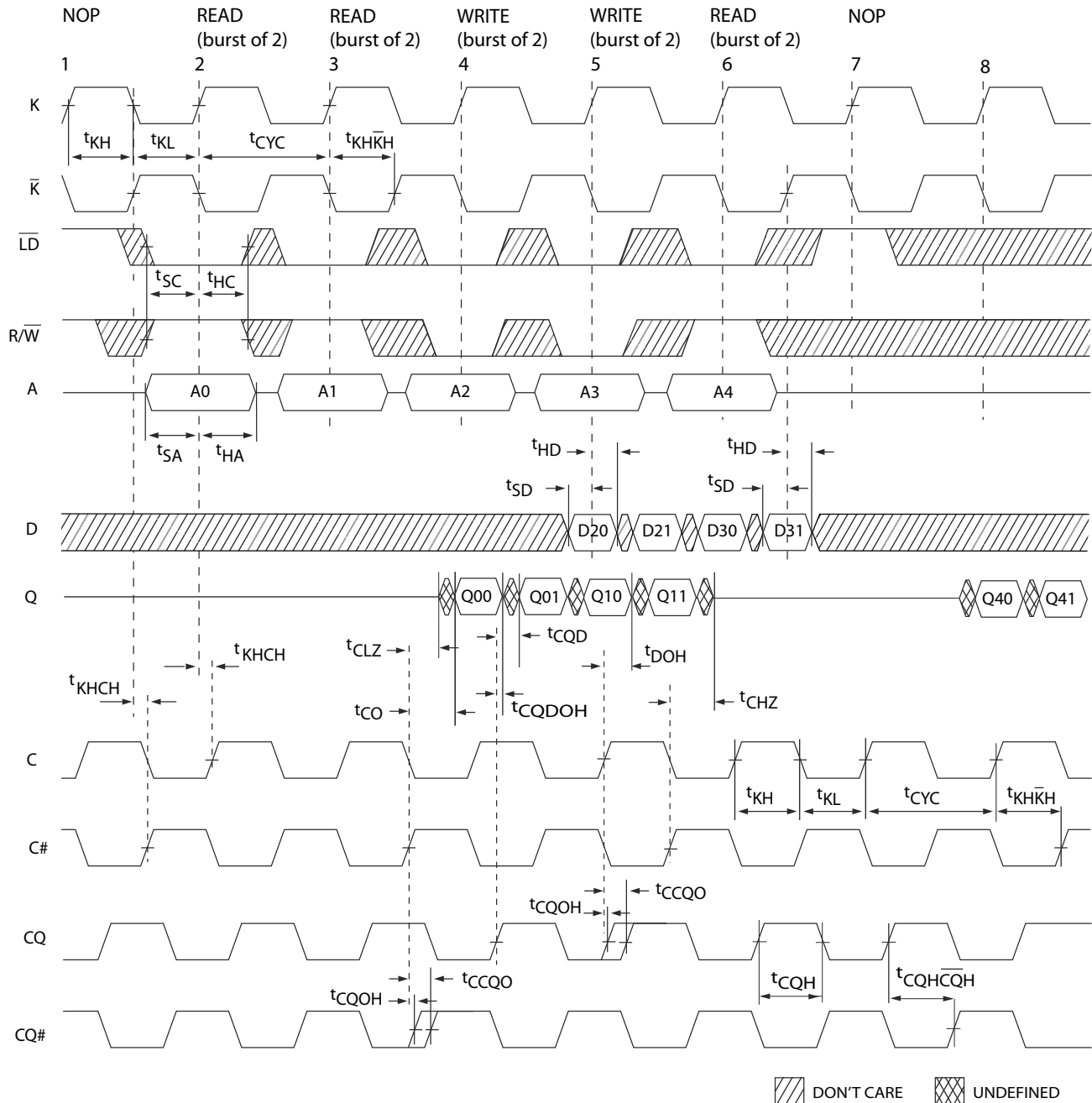
32. t_{CHZ} , t_{CLZ} , are specified with a load capacitance of 5 pF as in (b) of [Figure 5 on page 22](#). Transition is measured ± 100 mV from steady-state voltage.

33. At any voltage and temperature t_{CHZ} is less than t_{CLZ} and t_{CHZ} less than t_{CO} .

34. For frequencies 300 MHz or below, the Cypress QDR II devices surpass the QDR consortium specification for PLL lock time ($t_{KC\ lock}$) of 20 μs (min. spec.) and will lock after 1024 clock cycles (min. spec.), after a stable clock is presented, per the previous 90 nm version.

Switching Waveforms

Figure 6. Read/Write/Deselect Sequence [35, 36, 37]



Notes

35. Q00 refers to output from address A0. Q01 refers to output from the next internal burst address following A0, that is, A0 + 1.

36. Outputs are disabled (high Z) one clock cycle after a NOP.

37. In this example, if address A4 = A3, then data Q40 = D30 and Q41 = D31. Write data is forwarded immediately as read results. This note applies to the whole diagram.

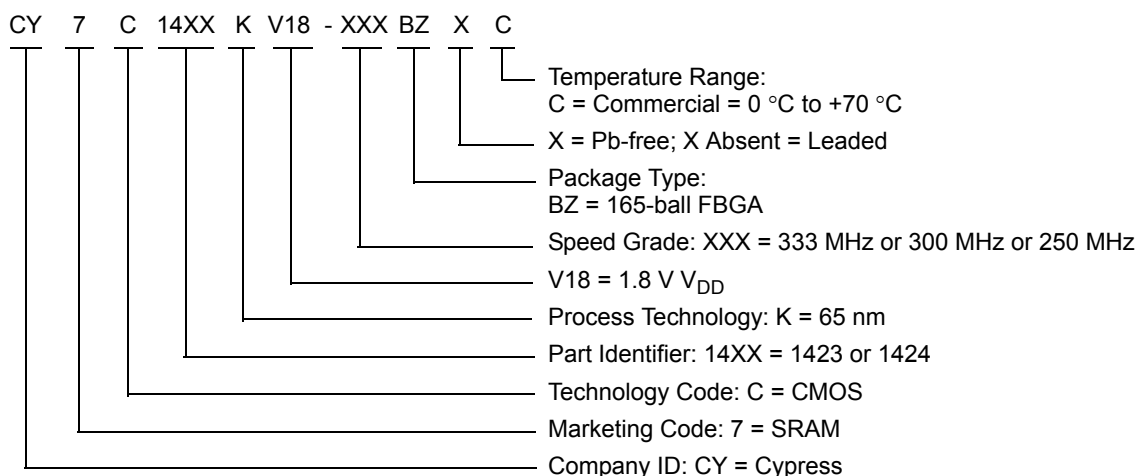
Ordering Information

The following table contains only the parts that are currently available. If you do not see what you are looking for, contact your local sales representative. For more information, visit the Cypress website at www.cypress.com and refer to the product summary page at <http://www.cypress.com/products>

Cypress maintains a worldwide network of offices, solution centers, manufacturer's representatives and distributors. To find the office closest to you, visit us at <http://www.cypress.com/go/datasheet/offices>.

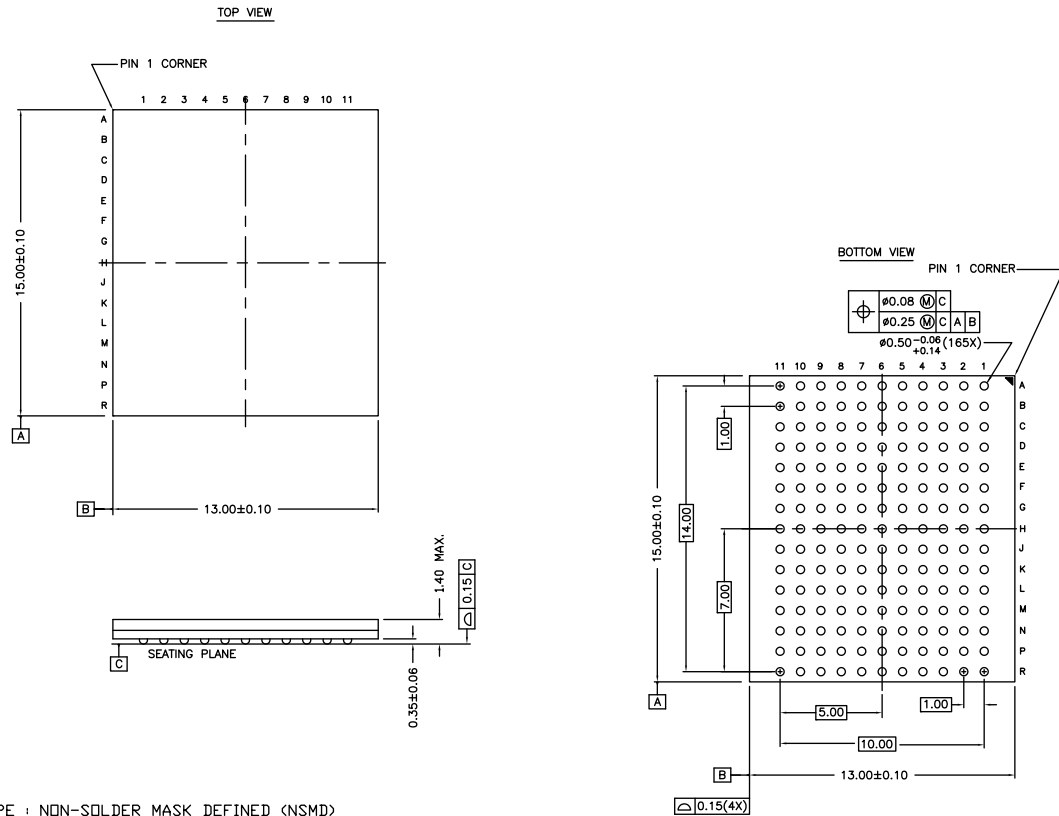
Speed (MHz)	Ordering Code	Package Diagram	Package Type	Operating Range
333	CY7C1423KV18-333BZXC	51-85180	165-ball FBGA (13 × 15 × 1.4 mm) Pb-free	Commercial
300	CY7C1423KV18-300BZC	51-85180	165-ball FBGA (13 × 15 × 1.4 mm)	Commercial
	CY7C1423KV18-300BZXC		165-ball FBGA (13 × 15 × 1.4 mm) Pb-free	
250	CY7C1423KV18-250BZC	51-85180	165-ball FBGA (13 × 15 × 1.4 mm)	Commercial
	CY7C1424KV18-250BZC			
	CY7C1423KV18-250BZXC		165-ball FBGA (13 × 15 × 1.4 mm) Pb-free	

Ordering Code Definitions



Package Diagram

Figure 7. 165-ball FBGA (13 × 15 × 1.4 mm) BB165D/BW165D (0.5 Ball Diameter) Package Outline, 51-85180



51-85180 *G

Acronyms

Acronym	Description
DDR	Double Data Rate
FBGA	Fine-Pitch Ball Grid Array
HSTL	High-Speed Transceiver Logic
I/O	Input/Output
JTAG	Joint Test Action Group
LMBU	Logical Multiple Bit Upset
LSB	Least Significant Bit
LSBU	Logical Single Bit Upset
MSB	Most Significant Bit
PLL	Phase Locked Loop
SEL	Single Event Latch-up
SRAM	Static Random Access Memory
TAP	Test Access Port
TCK	Test Clock
TMS	Test Mode Select
TDI	Test Data-In
TDO	Test Data-Out
TQFP	Thin Quad Flat Pack

Document Conventions

Units of Measure

Symbol	Unit of Measure
°C	degree Celsius
kΩ	kilohm
MHz	megahertz
μA	microampere
μs	microsecond
mA	milliampere
mm	millimeter
ms	millisecond
ns	nanosecond
Ω	ohm
%	percent
pF	picofarad
V	volt
W	watt

Document History Page

Document Title: CY7C1423KV18/CY7C1424KV18, 36-Mbit DDR II SIO SRAM Two-Word Burst Architecture Document Number: 001-57829				
Rev.	ECN	Orig. of Change	Submission Date	Description of Change
**	2816620	VKN / AESA	11/27/2009	New data sheet.
*A	3068457	NJY	10/21/2010	Changed status from Preliminary to Final. Added Ordering Code Definitions . Updated Package Diagram . Minor edits. Updated to new template.
*B	3167511	NJY	02/09/2011	Updated Switching Characteristics (Added Note 34 and referred the same note in description of $t_{KC\ lock}$ parameter). Updated Ordering Information . Added Acronyms and Units of Measure .
*C	3401884	PRIT	10/11/2011	Updated Pin Configurations (Changed part numbers from CY7C1423KV18 (4M × 18) and CY7C1424KV18 (2M × 36) to CY7C1423KV18 (2M × 18) and CY7C1424KV18 (1M × 36) in Figure 1).
*D	3609945	AVIA / PRIT	05/07/2012	Updated Features (Removed CY7C1422KV18, CY7C1429KV18 related information). Updated Configurations (Removed CY7C1422KV18, CY7C1429KV18 related information). Updated Functional Description (Removed CY7C1422KV18, CY7C1429KV18 related information). Updated Selection Guide (Removed 200 MHz, 167 MHz related information, removed CY7C1422KV18, CY7C1429KV18 related information). Removed Logic Block Diagram – CY7C1422KV18. Removed Logic Block Diagram – CY7C1429KV18. Updated Pin Configurations (Removed CY7C1422KV18, CY7C1429KV18 related information). Updated Pin Definitions (Removed CY7C1422KV18, CY7C1429KV18 related information). Updated Functional Overview (Removed CY7C1422KV18, CY7C1429KV18 related information). Updated Truth Table (Removed CY7C1422KV18, CY7C1429KV18 related information). Updated Write Cycle Descriptions (Removed CY7C1422KV18 related information). Removed Write Cycle Descriptions (Corresponding to CY7C1429KV18). Updated Identification Register Definitions (Removed CY7C1422KV18, CY7C1429KV18 related information). Updated Operating Range (Removed Industrial Temperature Range). Updated Electrical Characteristics (Updated DC Electrical Characteristics (Removed 200 MHz, 167 MHz related information, removed CY7C1422KV18, CY7C1429KV18 related information)). Updated Switching Characteristics (Removed 200 MHz, 167 MHz related information). Updated Package Diagram (spec 51-85180 (changed revision from *C to *E)).
*E	3793879	PRIT	10/25/2012	Updated Package Diagram (spec 51-85180 (Changed revision from *E to *F)).
*F	4373836	PRIT	05/08/2014	Updated Application Example : Updated Figure 2 . Updated Thermal Resistance : Updated values of Θ_{JA} parameter. Included Θ_{JB} parameter and its details. Updated to new template.

Document History Page *(continued)*

Document Title: CY7C1423KV18/CY7C1424KV18, 36-Mbit DDR II SIO SRAM Two-Word Burst Architecture Document Number: 001-57829				
Rev.	ECN	Orig. of Change	Submission Date	Description of Change
*G	4567876	PRIT	11/12/2014	Updated Functional Description : Added "For a complete list of related documentation, click here ." at the end. Updated Ordering Information : Updated part numbers.
*H	5063647	PRIT	12/24/2015	Updated Package Diagram : spec 51-85180 – Changed revision from *F to *G. Updated to new template. Completing Sunset Review.
*I	5523049	PRIT	11/16/2016	Updated Ordering Information : Updated part numbers. Updated to new template. Completing Sunset Review.
*J	6014023	AESATMP9	01/04/2018	Updated logo and copyright.

Sales, Solutions, and Legal Information

Worldwide Sales and Design Support

Cypress maintains a worldwide network of offices, solution centers, manufacturer's representatives, and distributors. To find the office closest to you, visit us at [Cypress Locations](#).

Products

Arm® Cortex® Microcontrollers	cypress.com/arm
Automotive	cypress.com/automotive
Clocks & Buffers	cypress.com/clocks
Interface	cypress.com/interface
Internet of Things	cypress.com/iot
Memory	cypress.com/memory
Microcontrollers	cypress.com/mcu
PSoC	cypress.com/psoc
Power Management ICs	cypress.com/pmic
Touch Sensing	cypress.com/touch
USB Controllers	cypress.com/usb
Wireless Connectivity	cypress.com/wireless

PSoC® Solutions

[PSoC 1](#) | [PSoC 3](#) | [PSoC 4](#) | [PSoC 5LP](#) | [PSoC 6 MCU](#)

Cypress Developer Community

[Community](#) | [Projects](#) | [Video](#) | [Blogs](#) | [Training](#) | [Components](#)

Technical Support

cypress.com/support

© Cypress Semiconductor Corporation, 2009-2018. This document is the property of Cypress Semiconductor Corporation and its subsidiaries, including Spansion LLC ("Cypress"). This document, including any software or firmware included or referenced in this document ("Software"), is owned by Cypress under the intellectual property laws and treaties of the United States and other countries worldwide. Cypress reserves all rights under such laws and treaties and does not, except as specifically stated in this paragraph, grant any license under its patents, copyrights, trademarks, or other intellectual property rights. If the Software is not accompanied by a license agreement and you do not otherwise have a written agreement with Cypress governing the use of the Software, then Cypress hereby grants you a personal, non-exclusive, nontransferable license (without the right to sublicense) (1) under its copyright rights in the Software (a) for Software provided in source code form, to modify and reproduce the Software solely for use with Cypress hardware products, only internally within your organization, and (b) to distribute the Software in binary code form externally to end users (either directly or indirectly through resellers and distributors), solely for use on Cypress hardware product units, and (2) under those claims of Cypress's patents that are infringed by the Software (as provided by Cypress, unmodified) to make, use, distribute, and import the Software solely for use with Cypress hardware products. Any other use, reproduction, modification, translation, or compilation of the Software is prohibited.

TO THE EXTENT PERMITTED BY APPLICABLE LAW, CYPRESS MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARD TO THIS DOCUMENT OR ANY SOFTWARE OR ACCOMPANYING HARDWARE, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE. No computing device can be absolutely secure. Therefore, despite security measures implemented in Cypress hardware or software products, Cypress does not assume any liability arising out of any security breach, such as unauthorized access to or use of a Cypress product. In addition, the products described in these materials may contain design defects or errors known as errata which may cause the product to deviate from published specifications. To the extent permitted by applicable law, Cypress reserves the right to make changes to this document without further notice. Cypress does not assume any liability arising out of the application or use of any product or circuit described in this document. Any information provided in this document, including any sample design information or programming code, is provided only for reference purposes. It is the responsibility of the user of this document to properly design, program, and test the functionality and safety of any application made of this information and any resulting product. Cypress products are not designed, intended, or authorized for use as critical components in systems designed or intended for the operation of weapons, weapons systems, nuclear installations, life-support devices or systems, other medical devices or systems (including resuscitation equipment and surgical implants), pollution control or hazardous substances management, or other uses where the failure of the device or system could cause personal injury, death, or property damage ("Unintended Uses"). A critical component is any component of a device or system whose failure to perform can be reasonably expected to cause the failure of the device or system, or to affect its safety or effectiveness. Cypress is not liable, in whole or in part, and you shall and hereby do release Cypress from any claim, damage, or other liability arising from or related to all Unintended Uses of Cypress products. You shall indemnify and hold Cypress harmless from and against all claims, costs, damages, and other liabilities, including claims for personal injury or death, arising from or related to any Unintended Uses of Cypress products.

Cypress, the Cypress logo, Spansion, the Spansion logo, and combinations thereof, WICED, PSoC, CapSense, EZ-USB, F-RAM, and Traveo are trademarks or registered trademarks of Cypress in the United States and other countries. For a more complete list of Cypress trademarks, visit cypress.com. Other names and brands may be claimed as property of their respective owners.

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Cypress Semiconductor:

[CY7C1424KV18-250BZC](#) [CY7C1423KV18-250BZC](#) [CY7C1423KV18-300BZXCT](#) [CY7C1424KV18-250BZCT](#)
[CY7C1423KV18-300BZC](#) [CY7C1424KV18-333BZC](#) [CY7C1423KV18-333BZXC](#) [CY7C1423KV18-250BZXC](#)
[CY7C1423KV18-300BZXC](#)